



Patent Application 10772,940

Docket No. 2001-1300/24061.413
Customer No. 42717

DFU

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kuan-Lun Chang, et al.	§	Docket No.:	2001-1300 / 24061.413
		§		
Serial No.:	10/772,940	§	Examiner:	Quoc Dinh Hoang
		§		
Filed:	February 5, 2004	§	Art Unit:	2818
		§		
For:	Method of Forming a Shallow	§	Conf. No.:	6082
	Trench-Deep Trench Isolation	§		
	Region for a BiCMOS/CMOS	§		
	Technology	§		

RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents
Mail Stop: Amendment
PO Box 1450
Alexandria, VA 22313-1450

Dear Sir:

The present paper is being submitted in response to the Restriction Requirement Office Action dated August 9, 2005 in the above-identified application.

Election of Claims begins on page 2 of this paper.

Amendments to the Claims are reflected in the Listing of Claims which begins on page 3 of this paper.

Remarks begin on page 11 of this paper.

I. Election

In the Office Action mailed August 9, 2005, the Examiner alleges that the application contains claims directed to two inventions and, thus, required restriction of either:

Group I: Claims 29-35, drawn to a shallow trench-deep trench structure in a semiconductor substrate; or

Group II: Claims 1-28, drawn to a process of making an isolation region in semiconductor substrate.

In response, Applicants hereby elect Group II, corresponding to claims 1-28. Applicants' election is made with traverse on the grounds that the embodiments delineated by the Examiner are not patentably distinct and therefore constitute a single invention concept.